TOSHIBA Field Effect Transistor Silicon P Channel MOS Type

SSM3J36FS

Power Management Switches

• 1.5-V drive

Low ON-resistance: R_{on} = 3.60 Ω (max) (@V_{GS} = -1.5 V)

: R_{on} = 2.70 Ω (max) (@V_{GS} = -1.8 V) : R_{on} = 1.60 Ω (max) (@V_{GS} = -2.8 V) : R_{on} = 1.31 Ω (max) (@V_{GS} = -4.5 V)

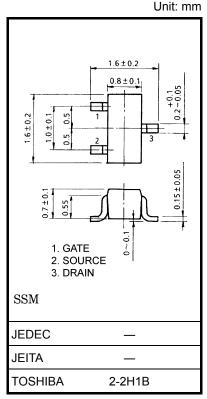
Absolute Maximum Ratings (Ta = 25 °C)

| Characteristics | | Symbol | Rating | Unit | |
|---------------------------|-------|------------------------|------------|------|--|
| Drain-source voltage | | V _{DSS} | -20 | V | |
| Gate-source voltage | | V _{GSS} | ±8 | V | |
| Drain current | DC | I _D | -330 | mA | |
| | Pulse | I _{DP} | -660 | | |
| Drain power dissipation | | P _D (Note1) | 150 | mW | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

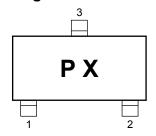
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note1: Mounted on an FR4 board (25.4 mm \times 25.4 mm \times 1.6mm, Cu Pad: 0.36 mm 2 \times 3)

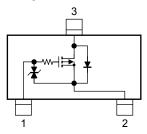


Weight: 2.4 mg (typ.)

Marking



Equivalent Circuit (top view)



Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Usage Considerations

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below –1 mA for the SSM3J36FS). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.

Take this into consideration when using the device.

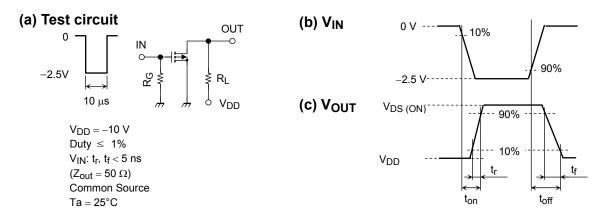


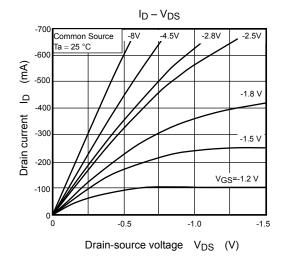
Electrical Characteristics (Ta = 25°C)

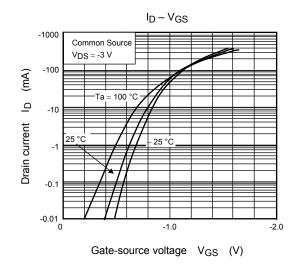
| Character | ristics | Symbol | Test Conditions | Min | Тур. | Max | Unit | |
|--------------------------------------|----------------------|---|---|------|------|------|------|--|
| Drain-source breakdown voltage | V _{(BR)DSS} | $I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$ | -20 | _ | _ | V | | |
| Diaiii-source breakdowii voitage | | V _{(BR)DSX} | $I_D = -1 \text{ mA}, V_{GS} = 8 \text{ V}$ | -12 | _ | | V | |
| Drain cutoff current | | I _{DSS} | $V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$ | _ | _ | -10 | μΑ | |
| Gate leakage curre | nt | I _{GSS} | $V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μА | |
| Gate threshold volta | age | V _{th} | $V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$ | -0.3 | _ | -1.0 | V | |
| Forward transfer ad | Imittance | Y _{fs} | $V_{DS} = -3 \text{ V}, I_D = -100 \text{mA}$ (Note2) | 190 | _ | _ | mS | |
| Drain-source ON-resistance | R _{DS} (ON) | $I_D = -100 \text{mA}, V_{GS} = -4.5 \text{ V}$ (Note2) | _ | 0.95 | 1.31 | Ω | | |
| | | $I_D = -80 \text{mA}, V_{GS} = -2.8 \text{ V}$ (Note2) | _ | 1.22 | 1.60 | | | |
| | | $I_D = -40 \text{mA}, V_{GS} = -1.8 \text{ V}$ (Note2) | _ | 1.80 | 2.70 | | | |
| | | $I_D = -30 \text{mA}, V_{GS} = -1.5 \text{ V}$ (Note2) | _ | 2.23 | 3.60 | | | |
| Input capacitance Output capacitance | | C _{iss} | V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz | _ | 43 | _ | pF | |
| | | C _{oss} | | _ | 10.3 | _ | | |
| Reverse transfer capacitance | | C _{rss} | | _ | 6.1 | _ | | |
| Total Gate Charge Q _g | | | _ | 1.2 | _ | | | |
| Gate-Source Charge | | Q_{gs} | V_{DS} = -10 V, I_{DS} = -330mA V_{GS} = -4 V | _ | 0.85 | _ | nC | |
| Gate-Drain Charge | | Q_{gd} | | _ | 0.35 | _ | | |
| Switching time | Turn-on time | t _{on} | V _{DD} = -10 V, I _D = -100mA | _ | 90 | _ | ns | |
| | Turn-off time | t _{off} | $V_{GS} = 0$ to -2.5 V, $R_G = 50\Omega$ | | 200 | _ | | |
| Drain-source forward voltage | | V _{DSF} | $I_D = 330 \text{mA}, V_{GS} = 0 \text{ V}$ (Note2) | _ | 0.88 | 1.2 | V | |

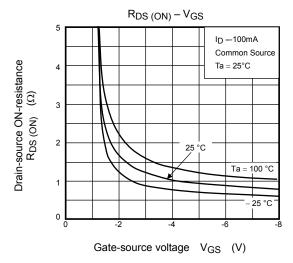
Note2: Pulse test

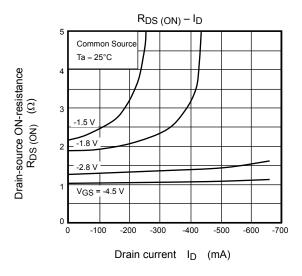
Switching Time Test Circuit

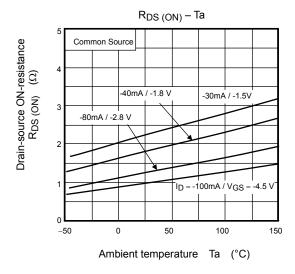


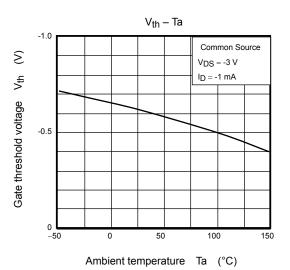


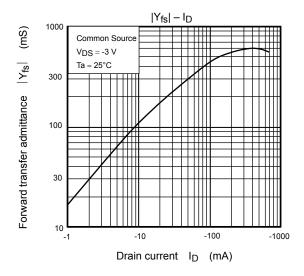


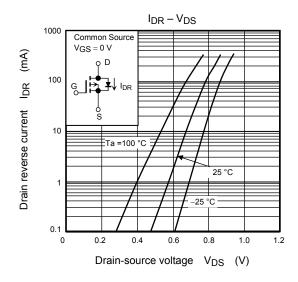


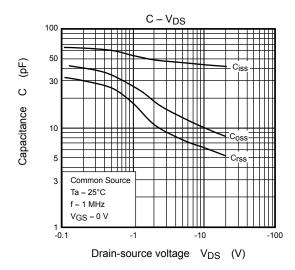


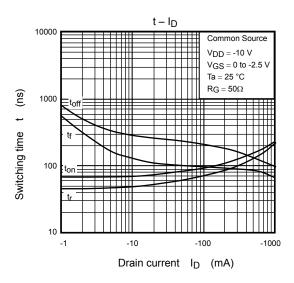


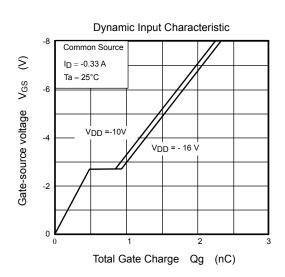


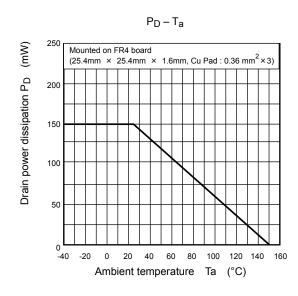












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